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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	24MHz
Connectivity	I ² C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, PDR, POR, PVD, PWM, Temp Sensor, WDT
Number of I/O	37
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 10x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f100c6t7b

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

2 Description

The STM32F100x4, STM32F100x6, STM32F100x8 and STM32F100xB microcontrollers incorporate the high-performance ARM[®] Cortex[®]-M3 32-bit RISC core operating at a 24 MHz frequency, high-speed embedded memories (Flash memory up to 128 Kbytes and SRAM up to 8 Kbytes), and an extensive range of enhanced peripherals and I/Os connected to two APB buses. All devices offer standard communication interfaces (up to two I²Cs, two SPIs, one HDMI CEC, and up to three USARTs), one 12-bit ADC, two 12-bit DACs, up to six general-purpose 16-bit timers and an advanced-control PWM timer.

The STM32F100xx low- and medium-density devices operate in the -40 to +85 °C and -40 to +105 °C temperature ranges, from a 2.0 to 3.6 V power supply.

A comprehensive set of power-saving mode allows the design of low-power applications.

These microcontrollers include devices in three different packages ranging from 48 pins to 100 pins. Depending on the device chosen, different sets of peripherals are included.

These features make these microcontrollers suitable for a wide range of applications such as application control and user interfaces, medical and hand-held equipment, PC and gaming peripherals, GPS platforms, industrial applications, PLCs, inverters, printers, scanners, alarm systems, video intercoms, and HVACs.





Figure 1. STM32F100xx value line block diagram

1. Peripherals not present in low-density value line devices.

2. AF = alternate function on I/O port pin.

3. $T_A = -40$ °C to +85 °C (junction temperature up to 105 °C) or $T_A = -40$ °C to +105 °C (junction temperature up to 125 °C).



2.2 Overview

2.2.1 ARM[®] Cortex[®]-M3 core with embedded Flash and SRAM

The ARM[®] Cortex[®]-M3 processor is the latest generation of ARM processors for embedded systems. It has been developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced system response to interrupts.

The ARM Cortex[®]-M3 32-bit RISC processor features exceptional code-efficiency, delivering the high-performance expected from an ARM core in the memory size usually associated with 8- and 16-bit devices.

The STM32F100xx value line family having an embedded ARM core, is therefore compatible with all ARM tools and software.

2.2.2 Embedded Flash memory

Up to 128 Kbytes of embedded Flash memory is available for storing programs and data.

2.2.3 CRC (cyclic redundancy check) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code from a 32-bit data word and a fixed generator polynomial.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a signature of the software during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.

2.2.4 Embedded SRAM

Up to 8 Kbytes of embedded SRAM accessed (read/write) at CPU clock speed with 0 wait states.

2.2.5 Nested vectored interrupt controller (NVIC)

The STM32F100xx value line embeds a nested vectored interrupt controller able to handle up to 41 maskable interrupt channels (not including the 16 interrupt lines of $Cortex^{\mbox{\ensuremath{\mathbb{R}}}}$ -M3) and 16 priority levels.

- Closely coupled NVIC gives low latency interrupt processing
- Interrupt entry vector table address passed directly to the core
- Closely coupled NVIC core interface
- Allows early processing of interrupts
- Processing of *late arriving* higher priority interrupts
- Support for tail-chaining
- Processor state automatically saved
- Interrupt entry restored on interrupt exit with no instruction overhead

This hardware block provides flexible interrupt management features with minimal interrupt latency.



Advanced-control timer (TIM1)

The advanced-control timer (TIM1) can be seen as a three-phase PWM multiplexed on 6 channels. It has complementary PWM outputs with programmable inserted dead times. It can also be seen as a complete general-purpose timer. The 4 independent channels can be used for:

- Input capture
- Output compare
- PWM generation (edge or center-aligned modes)
- One-pulse mode output

If configured as a standard 16-bit timer, it has the same features as the TIMx timer. If configured as the 16-bit PWM generator, it has full modulation capability (0-100%).

The counter can be frozen in debug mode.

Many features are shared with those of the standard TIM timers which have the same architecture. The advanced control timer can therefore work together with the TIM timers via the Timer Link feature for synchronization or event chaining.

General-purpose timers (TIM2, TIM3, TIM4, TIM15, TIM16 & TIM17)

There are six synchronizable general-purpose timers embedded in the STM32F100xx devices (see *Table 3* for differences). Each general-purpose timers can be used to generate PWM outputs, or as simple time base.

TIM2, TIM3, TIM4

STM32F100xx devices feature three synchronizable 4-channels general-purpose timers. These timers are based on a 16-bit auto-reload up/downcounter and a 16-bit prescaler. They feature 4 independent channels each for input capture/output compare, PWM or one-pulse mode output. This gives up to 12 input captures/output compares/PWMs on the largest packages.

The TIM2, TIM3, TIM4 general-purpose timers can work together or with the TIM1 advanced-control timer via the Timer Link feature for synchronization or event chaining.

TIM2, TIM3, TIM4 all have independent DMA request generation.

These timers are capable of handling quadrature (incremental) encoder signals and the digital outputs from 1 to 3 hall-effect sensors.

Their counters can be frozen in debug mode.

TIM15, TIM16 and TIM17

These timers are based on a 16-bit auto-reload upcounter and a 16-bit prescaler.

TIM15 has two independent channels, whereas TIM16 and TIM17 feature one single channel for input capture/output compare, PWM or one-pulse mode output.

The TIM15, TIM16 and TIM17 timers can work together, and TIM15 can also operate with TIM1 via the Timer Link feature for synchronization or event chaining.

TIM15 can be synchronized with TIM16 and TIM17.

TIM15, TIM16, and TIM17 have a complementary output with dead-time generation and independent DMA request generation





Figure 4. STM32F100xx value line LQFP64 pinout

Figure 5. STM32F100xx value line LQFP48 pinout





	Pi	ns						Alternate functions ⁽³⁾⁽⁴⁾	
LQFP100	LQFP64	TFBGA64	LQFP48	Pin name	Type ⁽¹⁾	I / O level ⁽²⁾	Main function ⁽³⁾ (after reset)	Default	Remap
33	24	H5	-	PC4	I/O	-	PC4	ADC1_IN14	-
34	25	H6	-	PC5	I/O	-	PC5	ADC1_IN15	-
35	26	F5	18	PB0	I/O	-	PB0	ADC1_IN8/TIM3_CH3 ⁽¹²⁾	TIM1_CH2N
36	27	G5	19	PB1	I/O	-	PB1	ADC1_IN9/TIM3_CH4 ⁽¹²⁾	TIM1_CH3N
37	28	G6	20	PB2	I/O	FT	PB2/BOOT1	-	-
38	-	-	-	PE7	I/O	FT	PE7	-	TIM1_ETR
39	-	-	-	PE8	I/O	FT	PE8	-	TIM1_CH1N
40	-	-	-	PE9	I/O	FT	PE9	-	TIM1_CH1
41	-	-	-	PE10	I/O	FT	PE10	-	TIM1_CH2N
42	-	-	-	PE11	I/O	FT	PE11	-	TIM1_CH2
43	-	-	-	PE12	I/O	FT	PE12	-	TIM1_CH3N
44	-	-	-	PE13	I/O	FT	PE13	-	TIM1_CH3
45	-	-	-	PE14	I/O	FT	PE14	-	TIM1_CH4
46	-	-	-	PE15	I/O	FT	PE15	-	TIM1_BKIN
47	29	G7	21	PB10	I/O	FT	PB10	I2C2_SCL ⁽⁹⁾ /USART3_TX (12)	TIM2_CH3 / HDMI_CEC
48	30	H7	22	PB11	I/O	FT	PB11	I2C2_SDA ⁽⁹⁾ /USART3_RX ⁽ 12)	TIM2_CH4
49	31	D6	23	V _{SS_1}	S	-	V _{SS_1}	-	-
50	32	E6	24	V _{DD_1}	S	-	V _{DD_1}	-	-
51	33	H8	25	PB12	I/O	FT	PB12	SPI2_NSS ⁽¹⁰⁾ / I2C2_SMBA ⁽⁹⁾ / TIM1_BKIN ⁽¹²⁾ /USART3_C K ⁽¹²⁾	-
52	34	G8	26	PB13	I/O	FT	PB13	SPI2_SCK ⁽¹⁰⁾ /TIM1_CH1N ⁽¹²⁾ USART3_CTS ⁽¹²⁾	-
53	35	F8	27	PB14	I/O	FT	PB14	SPI2_MISO ⁽¹⁰⁾ / TIM1_CH2N ⁽¹²⁾ / USART3_RTS ⁽¹²⁾	TIM15_CH1
54	36	F7	28	PB15	I/O	FT	PB15	SPI2_MOSI ⁽¹⁰⁾ / TIM1_CH3N / TIM15_CH1N ⁽¹²⁾	TIM15_CH2
55	-	-	-	PD8	I/O	FT	PD8	-	USART3_TX
56	-	-	-	PD9	I/O	FT	PD9	-	USART3_RX

Table 4. Low & me	dium-density STM32	F100xx pin definiti	ons (continued)
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	Pi	ns				<u></u>		Alternate function	s ⁽³⁾⁽⁴⁾
LQFP100	LQFP64	TFBGA64	LQFP48	Pin name	Type ⁽¹⁾	I / O level ⁽²	Main function ⁽³⁾ (after reset)	Default	Remap
79	52	B6	-	PC11	I/O	FT	PC11	-	USART3_RX
80	53	C5	-	PC12	I/O	FT	PC12	-	USART3_CK
81	-	C1	-	PD0	I/O	FT	PD0	-	-
82	-	D1	-	PD1	I/O	FT	PD1	-	-
83	54	B5	-	PD2	I/O	FT	PD2	TIM3_ETR	-
84	-	-	-	PD3	I/O	FT	PD3	-	USART2_CT S
85	-	-	-	PD4	I/O	FT	PD4	-	USART2_RT S
86	-	-	-	PD5	I/O	FT	PD5	-	USART2_TX
87	-	-	-	PD6	I/O	FT	PD6	-	USART2_RX
88	-	-	-	PD7	I/O	FT	PD7	-	USART2_CK
89	55	A5	39	PB3	I/O	FT	JTDO		TIM2_CH2 / PB3 TRACESWO SPI1_SCK
90	56	A4	40	PB4	I/O	FT	NJTRST	-	PB4 / TIM3_CH1 SPI1_MISO
91	57	C4	41	PB5	I/O	-	PB5	I2C1_SMBA / TIM16_BKIN	TIM3_CH2 / SPI1_MOSI
92	58	D3	42	PB6	I/O	FT	PB6	I2C1_SCL ⁽¹²⁾ / TIM4_CH1 ⁽¹¹⁾⁽¹²⁾ TIM16_CH1N	USART1_TX
93	59	C3	43	PB7	I/O	FT	PB7	I2C1_SDA ⁽¹²⁾ / TIM17_CH1N TIM4_CH2 ⁽¹¹⁾⁽¹²⁾	USART1_RX
94	60	B4	44	BOOT0	Ι	-	BOOT0	-	-
95	61	В3	45	PB8	I/O	FT	PB8	TIM4_CH3 ⁽¹¹⁾⁽¹²⁾ / TIM16_CH1 ⁽¹²⁾ / CEC ⁽¹²⁾	I2C1_SCL
96	62	A3	46	PB9	I/O	FT	PB9	TIM4_CH4 ⁽¹¹⁾⁽¹²⁾ / TIM17_CH1 ⁽¹²⁾	I2C1_SDA
97	-	-	-	PE0	I/O	FT	PE0	TIM4_ETR ⁽¹¹⁾	-
98	-	-	-	PE1	I/O	FT	PE1	-	-
99	63	D4	47	V _{SS_3}	S	-	V _{SS_3}	-	-
10 0	64	E4	48	V _{DD_3}	S	-	V _{DD_3}	-	-

Table 4. Low & medium-density STM32F100xx pin definitions (continued)





5.1.6 Power supply scheme





Caution: In *Figure 10*, the 4.7 μ F capacitor must be connected to V_{DD3}.



5.1.7 Current consumption measurement



Figure 11. Current consumption measurement scheme

5.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 5: Voltage characteristics*, *Table 6: Current characteristics*, and *Table 7: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Symbol	Ratings	Min	Max	Unit
$V_{DD} - V_{SS}$	External main supply voltage (including V_{DDA} and $V_{DD})^{\left(1\right)}$	-0.3	4.0	
$V_{IN}^{(2)}$	Input voltage on five volt tolerant pin	V _{SS} -0.3	V _{DD} +4.0	V
	Input voltage on any other pin	V _{SS} -0.3	4.0	
$ \Delta V_{DDx} $	Variations between different V_{DD} power pins	-	50	
$ V_{SSX} - V_{SS} $	Variations between all the different ground pins		50	mV
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	see Section 5. maximum rati sensi	-	

Table 5. Voltage characteristics

 All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.

2. V_{IN} maximum must always be respected. Refer to *Table 6: Current characteristics* for the maximum allowed injected current values.



Periphe	Current consumption (µA/MHz)	
	DMA1	22.92
AHB (up to 24MHz)	CRC	2,08
	BusMatrix ⁽²⁾	4,17
	APB1-Bridge	2,92
	TIM2	18,75
	TIM3	17,92
	TIM4	18,33
	TIM6	5,00
	TIM7	5,42
	SPI2/I2S2	4,17
	USART2	12,08
APB1 (up to 24MHz)	USART3	12,92
	I2C1	10,83
	I2C2	10,83
	CEC	5,83
	DAC ⁽³⁾	8,33
	WWDG	2,50
	PWR	2,50
	ВКР	3,33
	IWDG	7,50
	APB2-Bridge	3.75
	GPIOA	6,67
	GPIOB	6,25
	GPIOC	7,08
	GPIOD	6,67
	GPIOE	6,25
APB2 (up to 24MHz)	SPI1	4,17
	USART1	11,67
	TIM1	22,92
	TIM15	14,58
	TIM16	11,67
	TIM17	10.83
	ADC1 ⁽⁴⁾	15.83

Table 18. Peripheral current consumption⁽¹⁾

1. f_{HCLK} = 24 MHz, f_{APB1} = f_{HCLK} , fAPB2 = f_{HCLK} , default prescaler value for each peripheral.

2. The BusMatrix is automatically active when at least one master is ON.

- 3. When DAC_OUT1 or DAC_OU2 is enabled a current consumption equal to 0,5 mA must be added
- Specific conditions for ADC: f_{HCLK} = 24 MHz, f_{APB1} = f_{HCLK}, f_{APB2} = f_{HCLK}, f_{ADCCLK} = f_{APB2}/2. When ADON bit in the ADC_CR2 register is set to 1, a current consumption equal to 0, 1mA must be added.



5.3.9 Memory characteristics

Flash memory

The characteristics are given at T_{A} = –40 to 105 $^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min ⁽¹⁾	Тур	Max ⁽¹⁾	Unit
t _{prog}	16-bit programming time	$T_A = -40$ to +105 °C	40	52.5	70	μs
t _{ERASE}	Page (1 KB) erase time	$T_A = -40$ to +105 °C	20	-	40	ms
t _{ME}	Mass erase time	$T_A = -40$ to +105 °C	20	-	40	ms
I _{DD}		Read mode f _{HCLK} = 24 MHz, V _{DD} = 3.3 V	-	-	20	mA
	Supply current	Write / Erase modes f _{HCLK} = 24 MHz, V _{DD} = 3.3 V	-	-	5	mA
		Power-down mode / Halt, V _{DD} = 3.0 to 3.6 V	-	-	50	μA
V _{prog}	Programming voltage	-	2	-	3.6	V

Table 27.	Flash	memory	characteristics
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1. Guaranteed by design.

Symbol	Parameter	Conditions		Unit		
Symbol	Farameter	Conditions	Min ⁽¹⁾	Тур	Мах	Unit
N _{END}	Endurance	$T_A = -40$ to +85 °C (6 suffix versions) $T_A = -40$ to +105 °C (7 suffix versions)	10	-	-	kcycles
	Data retention	1 kcycle ⁽²⁾ at T _A = 85 °C	30	-	-	
t _{RET}		1 kcycle ⁽²⁾ at T _A = 105 °C	10	-	-	Years
		10 kcycles ⁽²⁾ at T _A = 55 °C	20	-	-	

Table 28. Flash memory endurance and data retention

1. Based on characterization not tested in production.

2. Cycling performed over the whole temperature range.



SPI interface characteristics

Unless otherwise specified, the parameters given in *Table 41* are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in *Table 8*.

Refer to Section 5.3.12: I/O current injection characteristics for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO).

Symbol	Parameter	Conditions	Min	Max	Unit
f _{scк}		Master mode	-	12	
1/t _{c(SCK)}	SFI Clock frequency	Slave mode	-	12	MHz
t _{r(SCK)} t _{f(SCK)}	SPI clock rise and fall time	Capacitive load: C = 30 pF		8	ns
DuCy(SCK)	SPI slave input clock duty cycle	Slave mode	30	70	%
t _{su(NSS)} ⁽¹⁾	NSS setup time	Slave mode	4t _{PCLK}	-	
t _{h(NSS)} ⁽¹⁾	NSS hold time	Slave mode	2t _{PCLK}	-	
t _{w(SCKH)} ⁽¹⁾ t _{w(SCKL)} ⁽¹⁾	SCK high and low time	Master mode, f _{PCLK} = 24 MHz, presc = 4	50	60	
t _{su(MI)} (1)	Data input satur timo	Master mode	5	-	
t _{su(SI)} ⁽¹⁾		Slave mode	5	-	1
t _{h(MI)} ⁽¹⁾	Data input hold time	Master mode	5	-	
t _{h(SI)} ⁽¹⁾		Slave mode	4	-	ns
t _{a(SO)} ⁽¹⁾⁽²⁾	Data output access time	Slave mode, f _{PCLK} = 24 MHz	0	3t _{PCLK}	
t _{dis(SO)} ⁽¹⁾⁽³⁾	Data output disable time	Slave mode	2	10	
t _{v(SO)} ⁽¹⁾	Data output valid time	Slave mode (after enable edge)	-	25	
t _{v(MO)} ⁽¹⁾	Data output valid time	Master mode (after enable edge)	-	5	
t _{h(SO)} ⁽¹⁾		Slave mode (after enable edge)	15	-	
t _{h(MO)} ⁽¹⁾	Data output hold time	Master mode (after enable edge)	2	-	

1. Guaranteed by characterization results.

2. Min time is for the minimum time to drive the output and the max time is for the maximum time to validate the data.

3. Min time is for the minimum time to invalidate the output and the max time is for the maximum time to put the data in Hi-Z





Figure 34. Power supply and reference decoupling (V_{REF+} not connected to V_{DDA})

1. $V_{\text{REF+}}$ is available on 100-pin packages and on TFBGA64 packages. $V_{\text{REF-}}$ is available on 100-pin packages only.



Figure 35. Power supply and reference decoupling (V_{REF+} connected to V_{DDA})

1. V_{REF+} and V_{REF-} inputs are available only on 100-pin packages.



Symbol	Parameter	Min	Тур	Max ⁽¹⁾	Unit	Comments		
	Offset error		-	±10	mV	Given for the DAC in 12-bit configuration		
Offset ⁽¹⁾	(difference between measured value at Code (0x800) and the	-	-	±3	LSB	Given for the DAC in 10-bit at V _{REF+} = 3.6 V		
	ideal value = V _{REF+} /2)		-	±12	LSB	Given for the DAC in 12-bit at V_{REF+} = 3.6 V		
Gain error ⁽¹⁾	Gain error	-	-	±0.5	%	Given for the DAC in 12bit configuration		
tsettling ⁽¹⁾	Settling time (full scale: for a 10- bit input code transition between the lowest and the highest input codes when DAC_OUT reaches final value ±1LSB	-	3	4	μs	$C_{LOAD} \le 50 \text{ pF}, \text{ R}_{LOAD} \ge 5 \text{ k}\Omega$		
Update rate ⁽¹⁾	Max frequency for a correct DAC_OUT change when small variation in the input code (from code i to i+1LSB)	-	-	1	MS/s	$C_{LOAD} \le 50 \text{ pF}, \text{ R}_{LOAD} \ge 5 \text{ k}\Omega$		
t _{wakeup} (1)	Wakeup time from off state (Setting the ENx bit in the DAC Control register)	-	6.5	10	μs	$C_{LOAD} \le 50 \text{ pF}, R_{LOAD} \ge 5 \text{ k}\Omega$ input code between lowest and highest possible ones.		
PSRR+ ⁽¹⁾	Power supply rejection ratio (to V _{DDA}) (static DC measurement	-	-67	-40	dB	No R _{LOAD} , C _{LOAD} = 50 pF		

1. Guaranteed by characterization results.

2. Guaranteed by design.



Figure 36.	12-bit	buffered	/non-buffered	DAC
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 The DAC integrates an output buffer that can be used to reduce the output impedance and to drive external loads directly without the use of an external operational amplifier. The buffer can be bypassed by configuring the BOFFx bit in the DAC_CR register.



6.2 LQFP64 package information

Figure 40.LQFP64 – 10 x 10 mm 64 pin low-profile quad flat package outline



1. Drawing is not in scale.

Table 49. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package
mechanical data

Symbol		millimeters			inches ⁽¹⁾	
Symbol	Min	Тур	Max	Min	Тур	Max
А	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
с	0.090	-	0.200	0.0035	-	0.0079
D	-	12.000	-	-	0.4724	-
D1	-	10.000	-	-	0.3937	-
D3	-	7.500	-	-	0.2953	-
E	-	12.000	-	-	0.4724	-
E1	-	10.000	-	-	0.3937	-
E3	-	7.500	-	-	0.2953	-



Symbol		millimeters			inches ⁽¹⁾	
	Min	Тур	Мах	Min	Тур	Мах
е	-	0.500	-	-	0.0197	-
К	0°	3.5°	7°	0°	3.5°	7°
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
CCC	-	-	0.080	-	-	0.0031

Table 49. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat packagemechanical data (continued)

1. Values in inches are converted from mm and rounded to 4 decimal digits.





1. Dimensions are in millimeters.



Device marking for LQFP64

The following figure gives an example of topside marking and pin 1 position identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.



Figure 42. LQFP64 marking example (package top view)

 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.



Table 50. TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch, thin profile fine pitch ballgrid array package mechanical data

Querra ha a l		millimeters			inches ⁽¹⁾	
Symbol	Min	Тур	Max	Min	Тур	Max
E1	-	3.500	-	-	0.1378	-
е	-	0.500	-	-	0.0197	-
F	-	0.750	-	-	0.0295	-
ddd	-	-	0.080	-	-	0.0031
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 44. TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch, thin profile fine pitch ball grid array, recommended footprint



Table 51. TFBGA64 recommended PCB design rules (0.5 mm pitch BGA) Image: Comparison of the second secon

Dimension	Recommended values
Pitch	0.5
Dpad	0.280 mm
Dsm	0.370 mm typ. (depends on the soldermask registration tolerance)
Stencil opening	0.280 mm
Stencil thickness	Between 0.100 mm and 1.125 mm
Pad trace width	0.100 mm



R8_FP_V1

6.5 Thermal characteristics

The maximum chip junction temperature (T_Jmax) must never exceed the values given in *Table 8: General operating conditions on page 34*.

The maximum chip-junction temperature, $T_{\rm J}$ max, in degrees Celsius, may be calculated using the following equation:

$$T_J max = T_A max + (P_D max x \Theta_{JA})$$

Where:

- T_A max is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in ° C/W,
- P_D max is the sum of P_{INT} max and P_{I/O} max (P_D max = P_{INT} max + P_{I/O}max),
- P_{INT} max is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.

 $\mathsf{P}_{\mathsf{I}/\mathsf{O}}$ max represents the maximum power dissipation on output pins where:

$$\mathsf{P}_{\mathsf{I}/\mathsf{O}} \max = \Sigma \; (\mathsf{V}_{\mathsf{OL}} \times \mathsf{I}_{\mathsf{OL}}) + \Sigma ((\mathsf{V}_{\mathsf{DD}} - \mathsf{V}_{\mathsf{OH}}) \times \mathsf{I}_{\mathsf{OH}}),$$

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Symbol	Parameter	Value	Unit
Θ _{JA}	Thermal resistance junction-ambient LQFP 100 - 14 × 14 mm / 0.5 mm pitch	46	°C/W
	Thermal resistance junction-ambient LQFP 64 - 10 × 10 mm / 0.5 mm pitch	45	
	Thermal resistance junction-ambient TFBGA64 - 5 × 5 mm / 0.5 mm pitch	65	
	Thermal resistance junction-ambient LQFP 48 - 7 × 7 mm / 0.5 mm pitch	55	

Table 53. Package thermal characteristics

6.5.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.



Date	Revision	Changes
30-Mar-2010	3	Revision history corrected. Updated <i>Table 6: Current characteristics</i> Values and note updated in <i>Table 16: Typical current consumption in</i> <i>Run mode, code with data processing running from Flash</i> and <i>Table 17: Typical current consumption in Sleep mode, code running</i> <i>from Flash or RAM.</i> Updated <i>Table 15: Typical and maximum current consumptions in Stop</i> <i>and Standby modes</i> Added <i>Figure 14: Typical current consumption on VBAT with RTC on</i> <i>vs. temperature at different VBAT values</i> Typical consumption for ADC1 corrected in <i>Table 18: Peripheral</i> <i>current consumption.</i> <i>Maximum current consumption</i> and <i>Typical current consumption:</i> frequency conditions corrected. <i>Output driving current</i> corrected. Updated <i>Table 30: EMI characteristics</i> <i>f_{ADC}</i> max corrected in <i>Table 42: ADC characteristics.</i> Small text changes.
06-May-2010	4	Updated Table 31: ESD absolute maximum ratings on page 55 and Table 32: Electrical sensitivities on page 56 Updated Table 44: ADC accuracy - limited test conditions on page 70 and Table 45: ADC accuracy on page 70
12-Jul-2010	5	Updated Table 24: LSI oscillator characteristics on page 51 Updated Table 44: ADC accuracy - limited test conditions on page 70 and Table 45: ADC accuracy on page 70
04-Apr-2011	6	Updated <i>Figure 2: Clock tree</i> to add FLITF clock Updated footnotes below <i>Table 5: Voltage characteristics on page 33</i> and <i>Table 6: Current characteristics on page 34</i> Updated tw min in <i>Table 19: High-speed external user clock</i> <i>characteristics on page 46</i> Updated startup time in <i>Table 22: LSE oscillator characteristics (fLSE</i> = 32.768 kHz) on page 49 Updated <i>Table 23: HSI oscillator characteristics on page 50</i> Added Section 5.3.12: I/O current injection characteristics on page 56 Updated <i>Table 34: I/O static characteristics on page 57</i> Corrected TTL and CMOS designations in <i>Table 35: Output voltage</i> <i>characteristics on page 60</i> Removed note on remapped characteristics from <i>Table 41: SPI</i> <i>characteristics on page 66</i>

Table 55. Document revision history (continued)



